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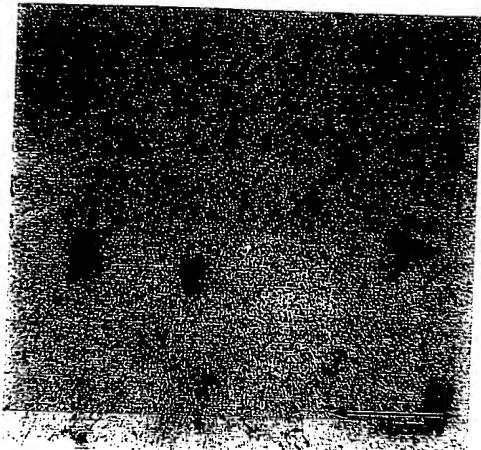


Fig. 1A

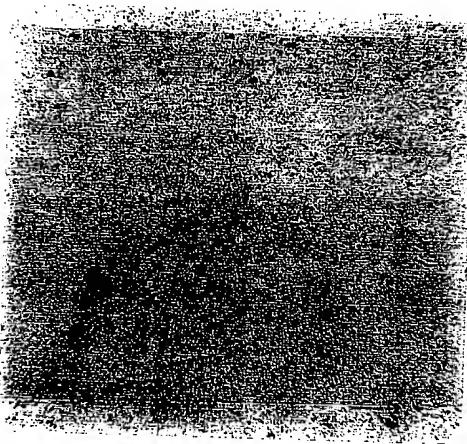


Fig. 1B

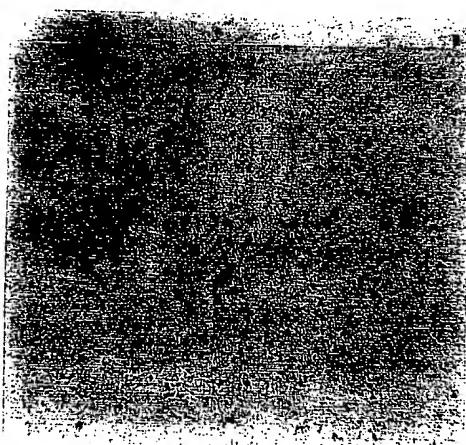


Fig. 1C

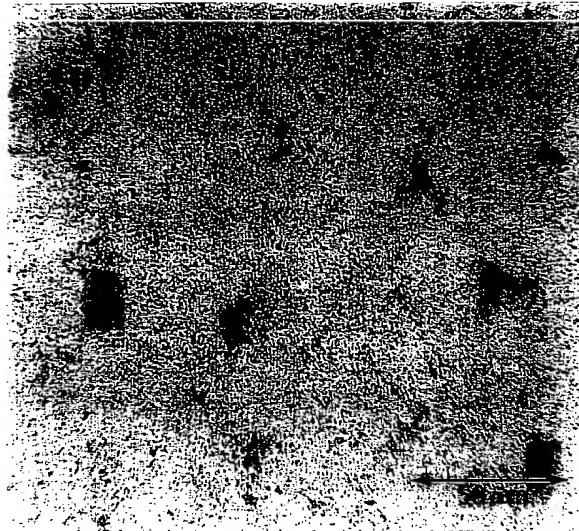


Fig. 2A



Fig. 2B

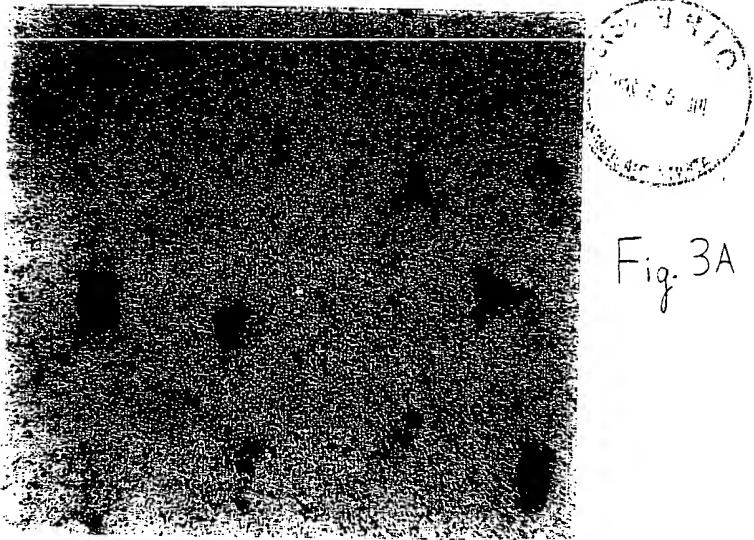


Fig. 3A

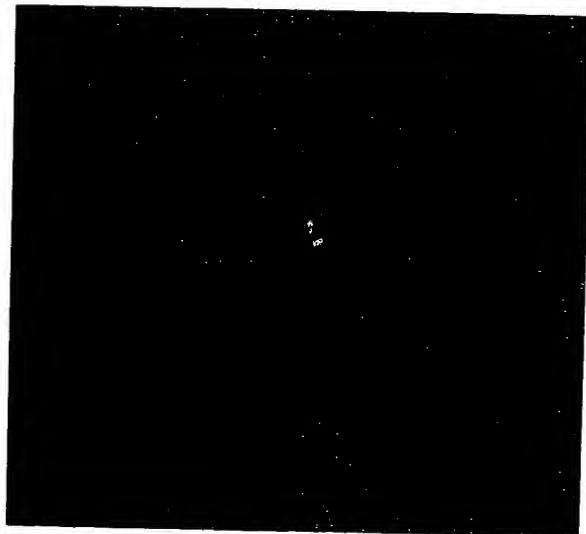
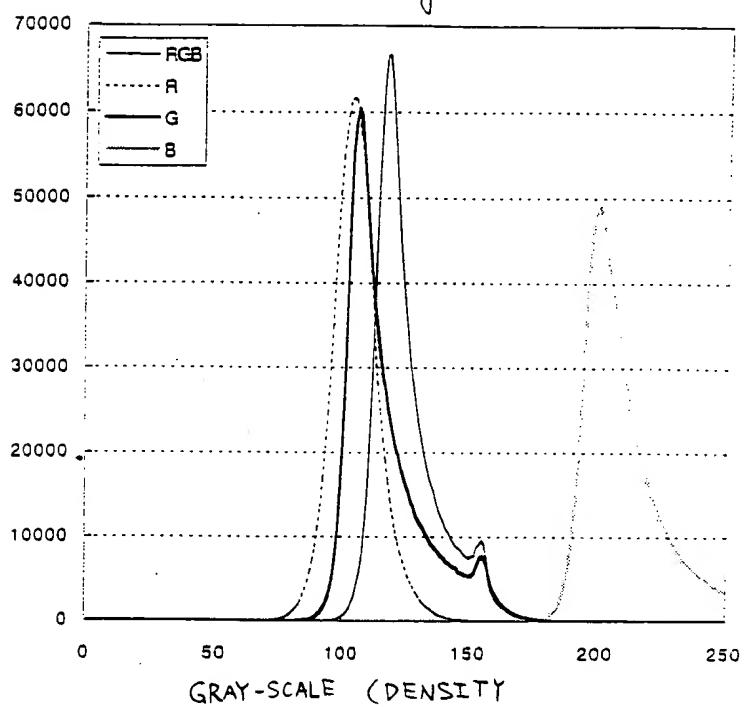


Fig. 3B



Fig. 4



1973
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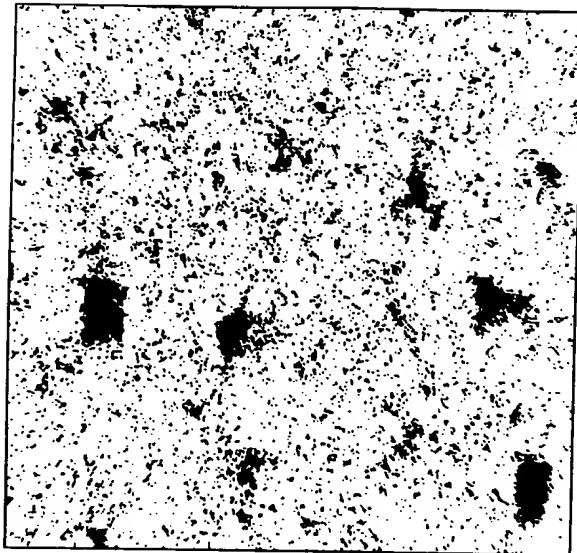


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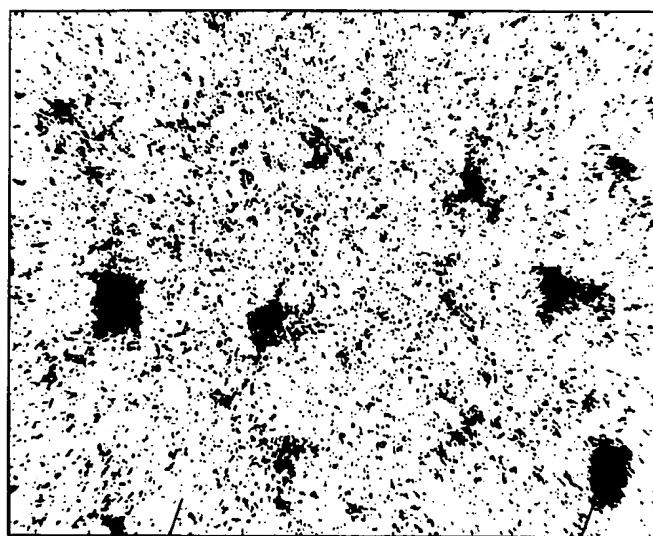


Fig. 5B

5001

5002

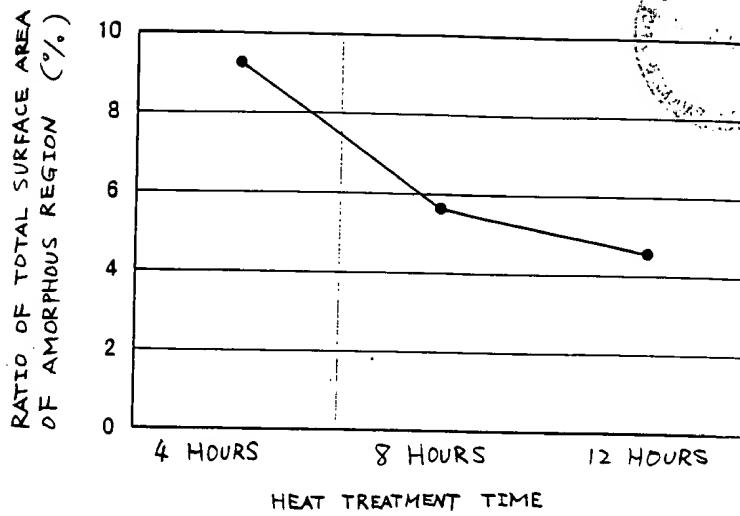


Fig. 6A

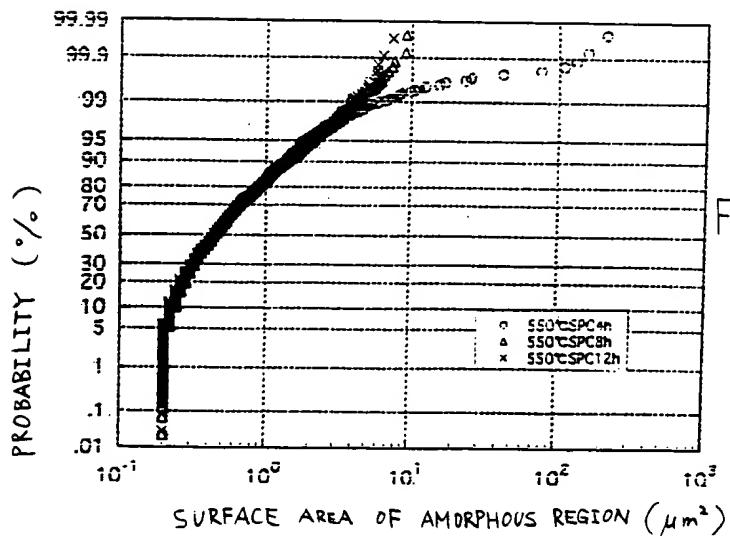


Fig. 6B

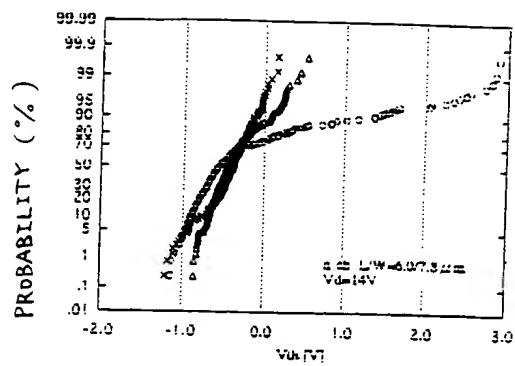


Fig. 7A

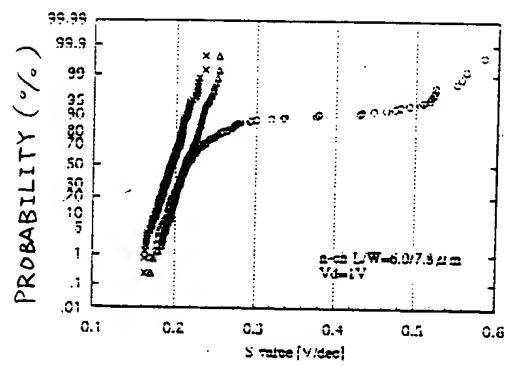


Fig. 7B

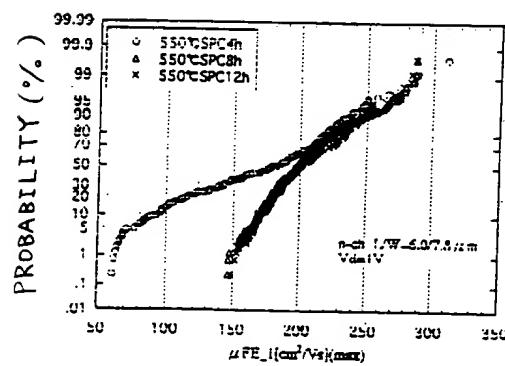


Fig. 7C

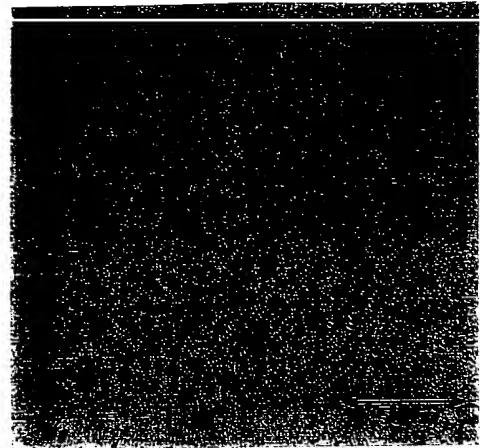


Fig. 8A

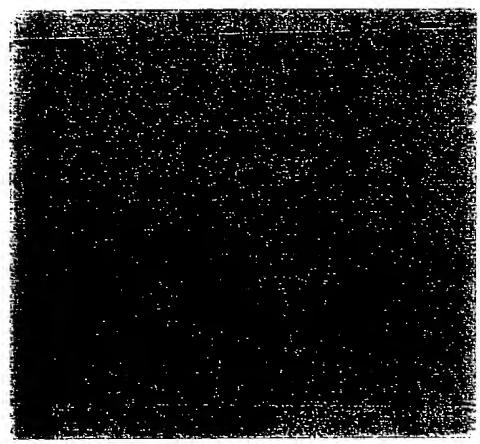


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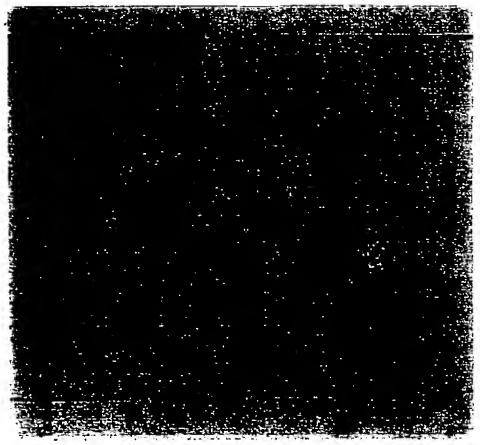


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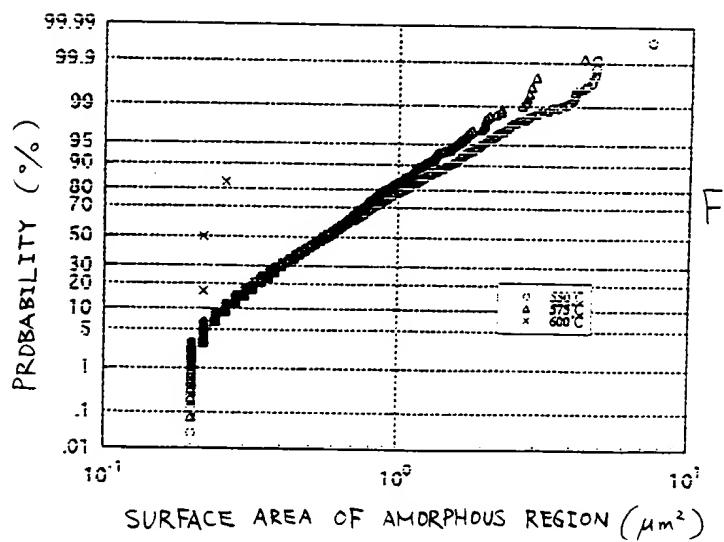
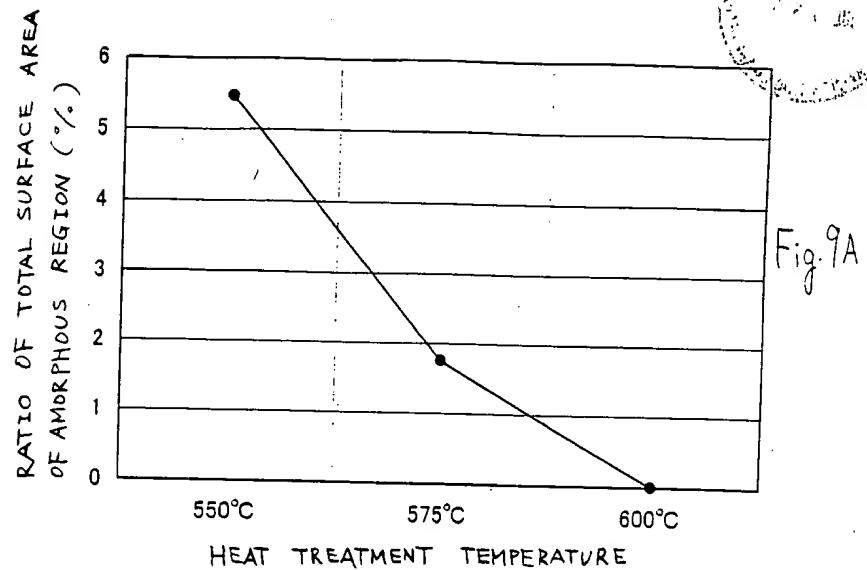


Fig. 10A

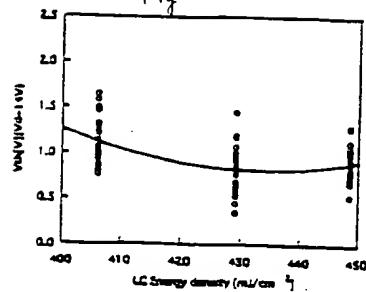


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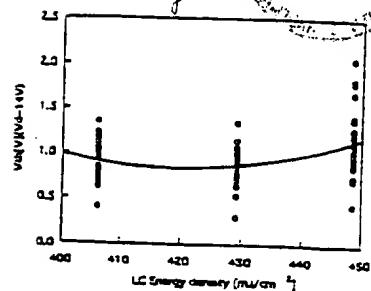


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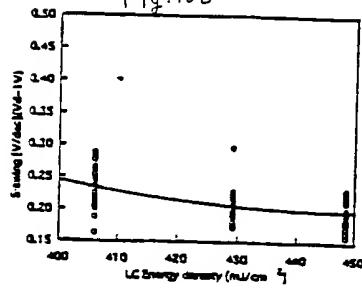


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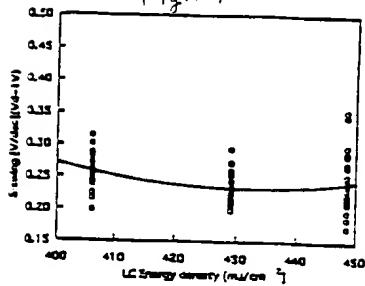


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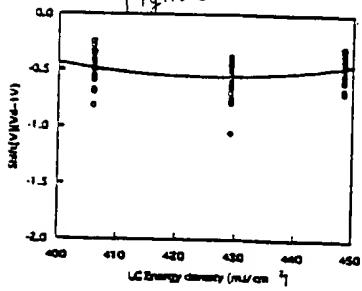


Fig. 10G

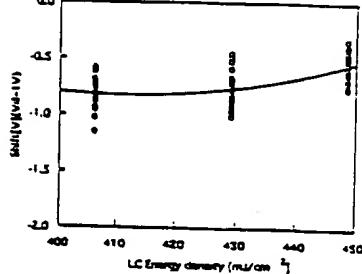


Fig. 10d

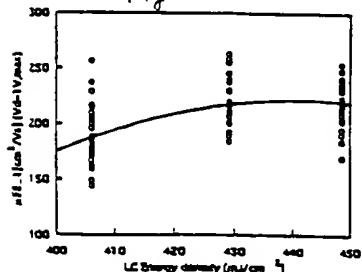


Fig. 10H

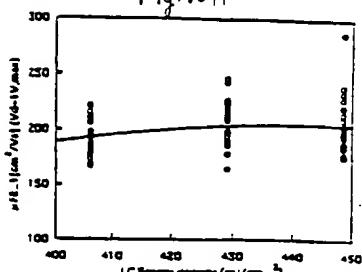


Fig. II A

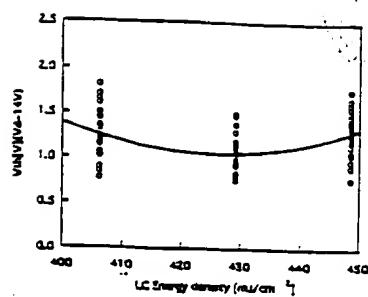


Fig. II B

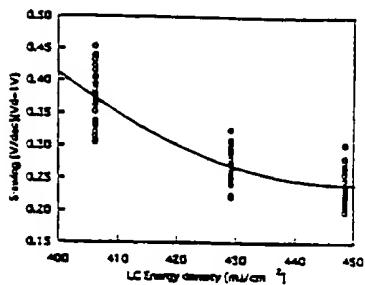


Fig. II C

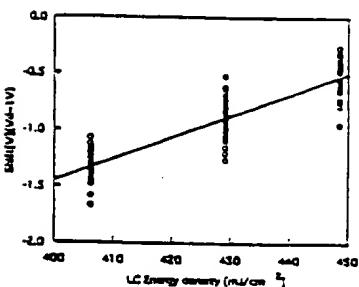
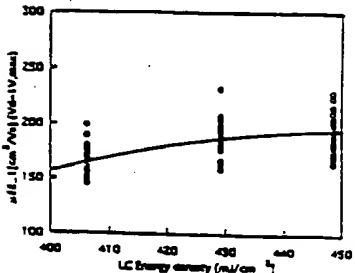
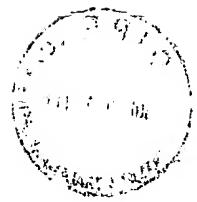
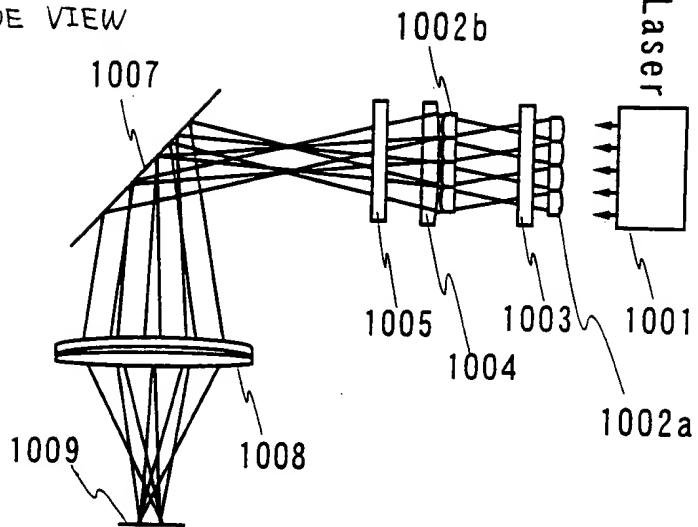


Fig. II d





SIDE VIEW



TOP VIEW

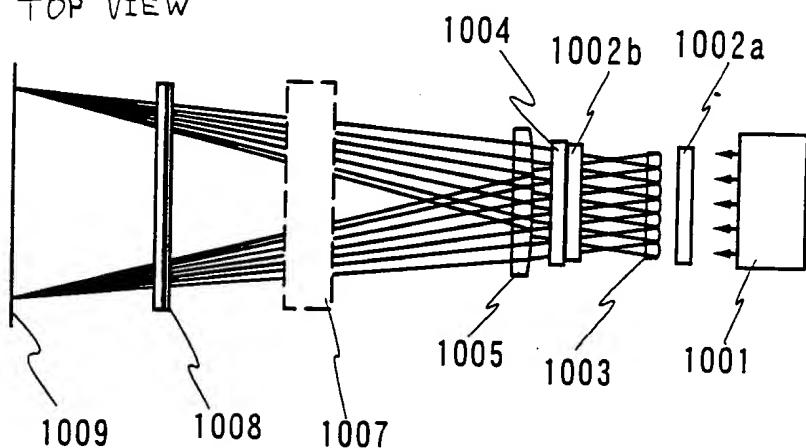


Fig. 12



Fig. 13

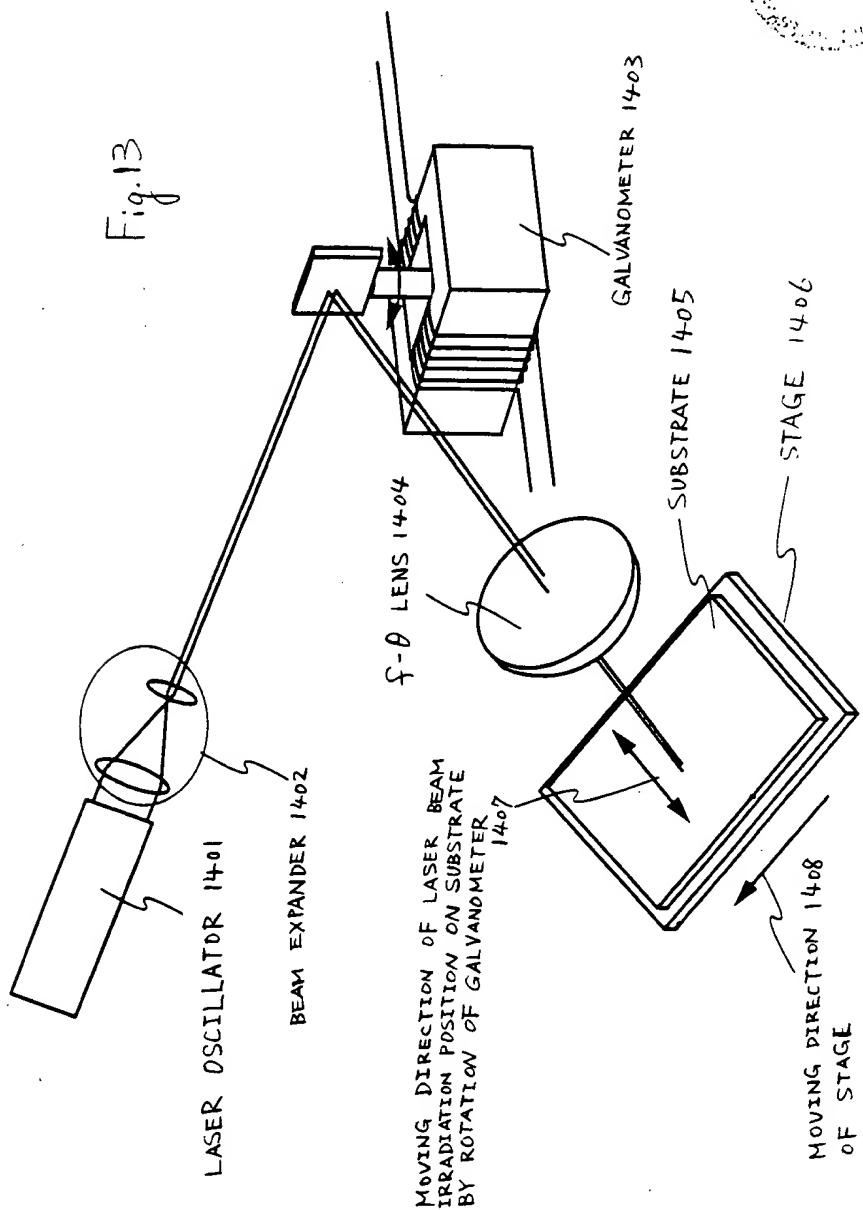


Fig. 14A STEP OF FORMING AMORPHOUS SEMICONDUCTOR FILM

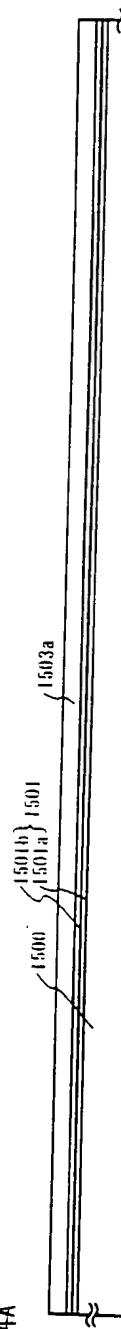


Fig. 14B FORMATION OF METAL CONTAINING LAYER / HEAT TREATMENT

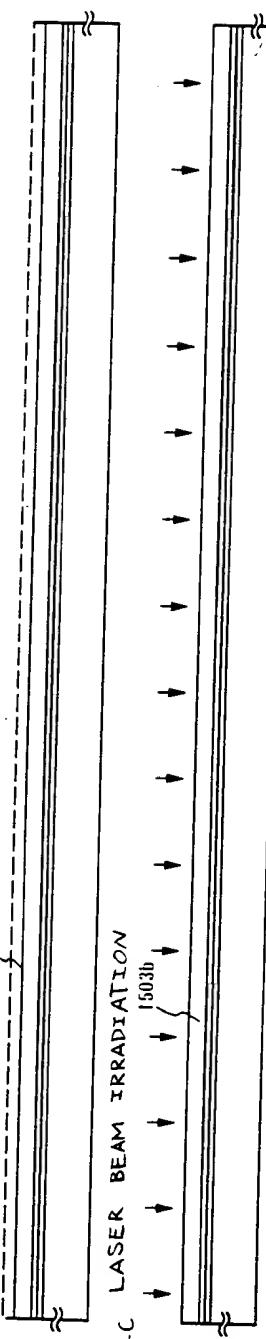


Fig. 14C LASER BEAM IRRADIATION

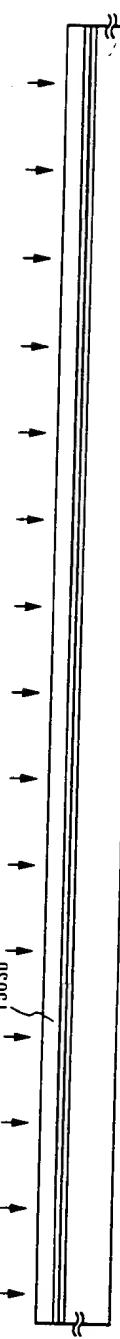


Fig. 14D STEP OF FORMING MASK LAYER

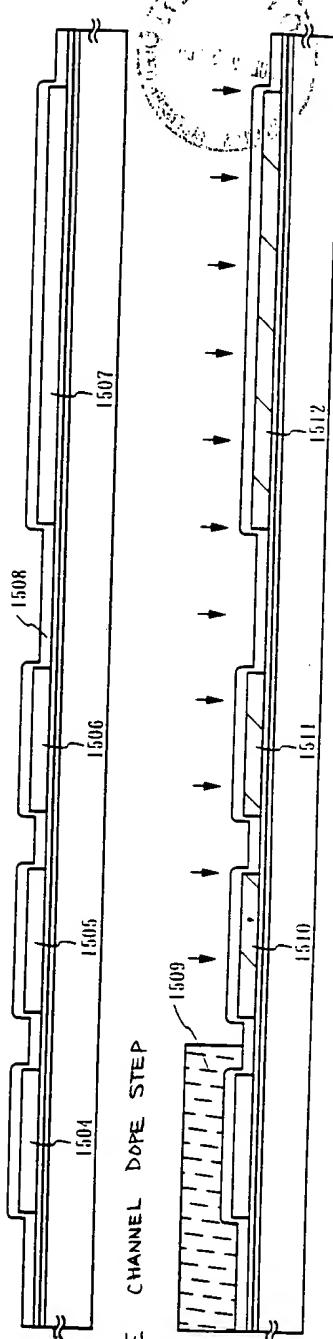


Fig. 14E CHANNEL DOPE STEP

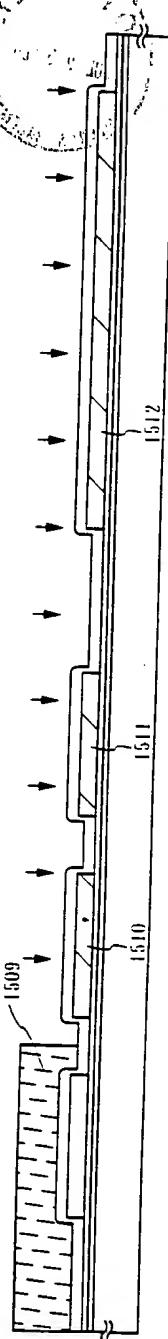


Fig.15A n⁻ DOPE STEP

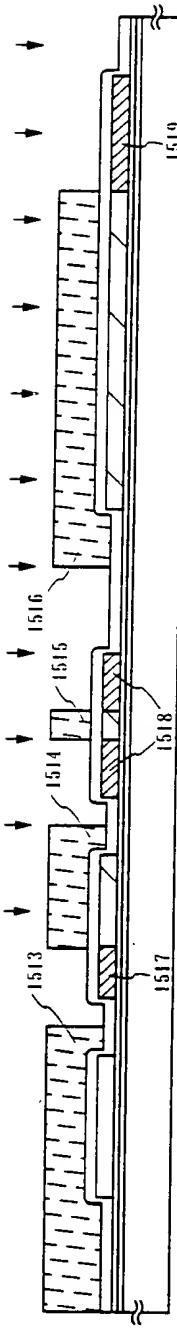


Fig.15B STEP OF REMOVING MASK LAYER/LASER ACTIVATION STEP/STEP OF FORMING GATE INSULATING FILM

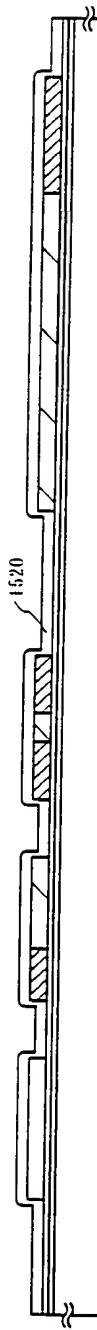


Fig.15C STEP OF FORMING FIRST CONDUCTIVE LAYER

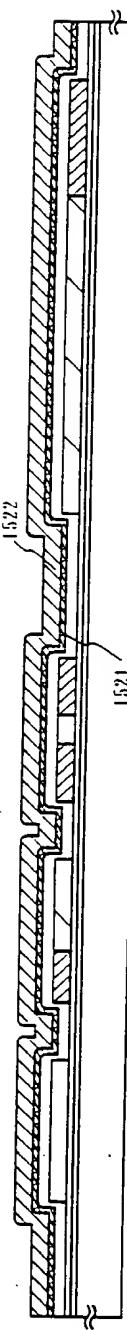


Fig.15D STEP OF FORMING GATE ELECTRODE

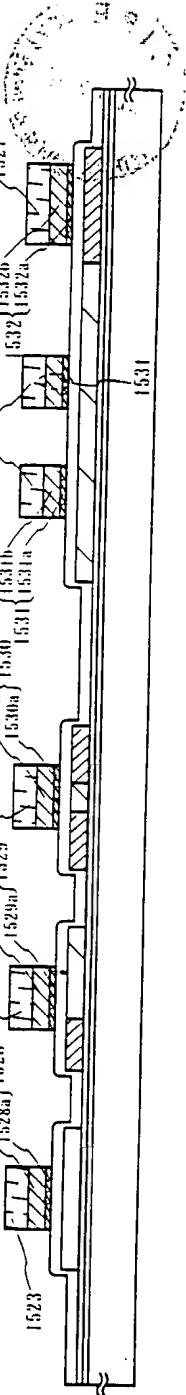


Fig. 16A P^{++} DOPING STEP

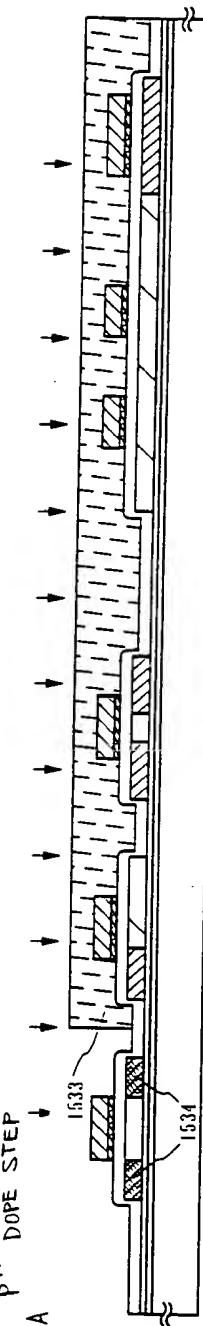


Fig. 16B n^+ DOPING STEP

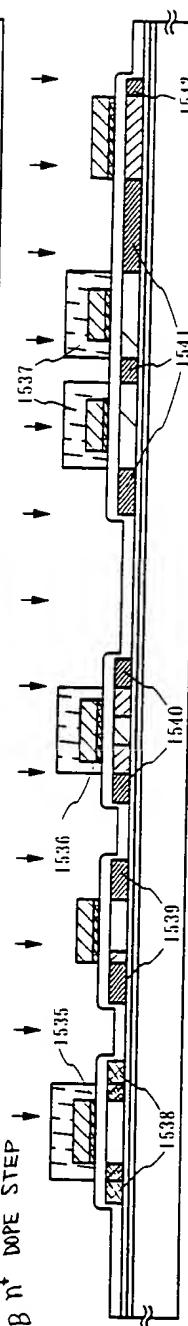


Fig. 16C n^- DOPING STEP

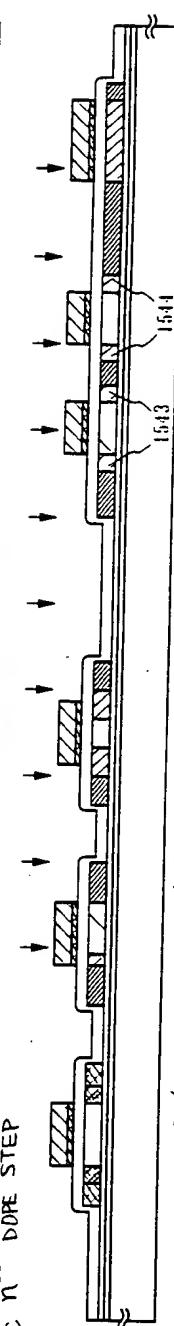
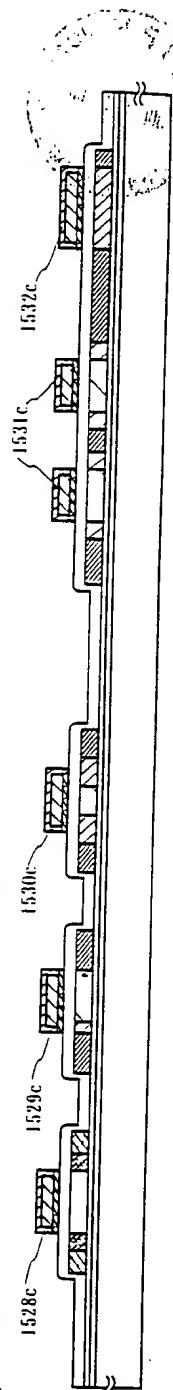


Fig. 16D ACTIVATION STEP / NITRIDING STEP / HYDROGENATION STEP



STEP OF FORMING SECOND CONDUCTIVE FILM

Fig. 17A

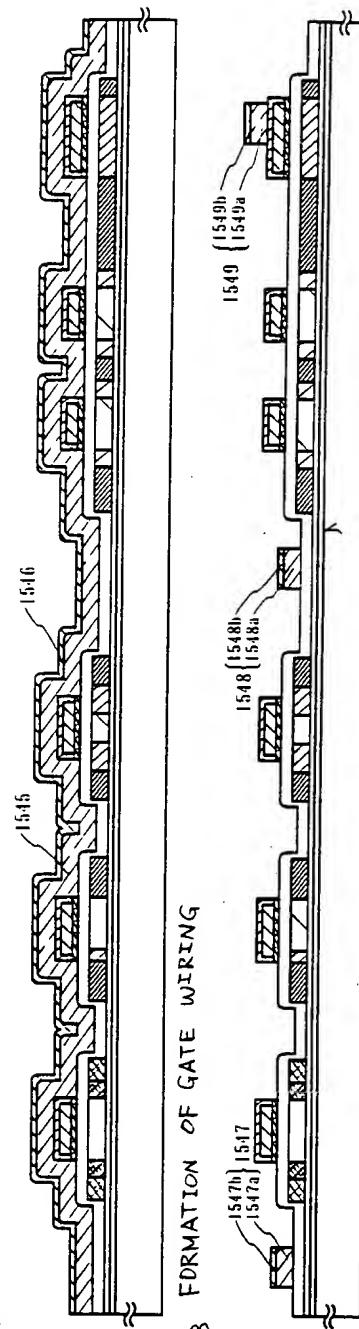


Fig. 17B FORMATION OF GATE WIRING

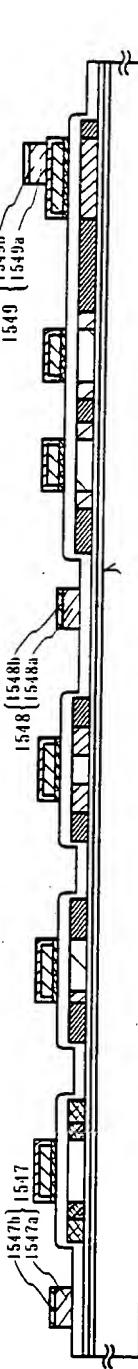


Fig. 17C STEP OF FORMING INTERLAYER INSULATING FILM/STEP OF FORMING CONTACT HOLE/STEP OF FORMING WIRING/ STEP OF FORMING PASSIVATION FILM

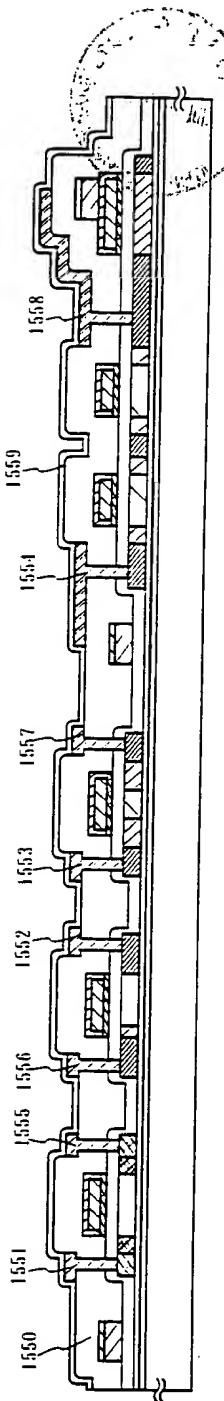
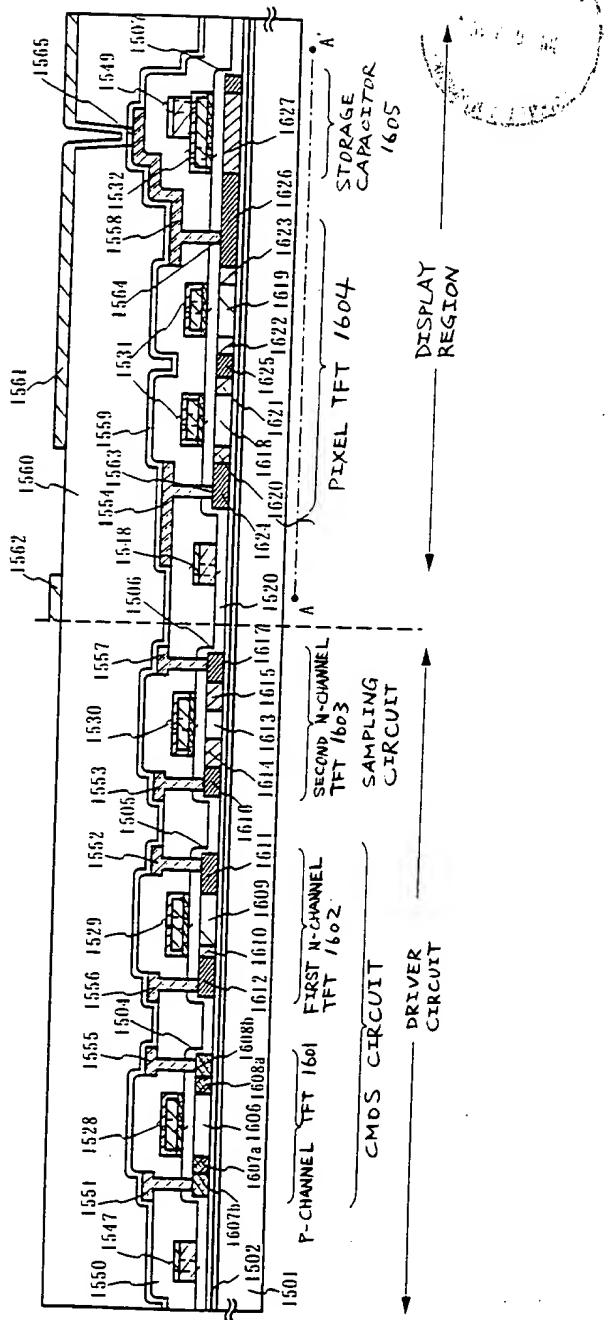


Fig. 18 STEP OF FORMING RESIN FILM/STEP OF FORMING CONTACT HOLE/
STEP OF FORMING PIXEL ELECTRODE



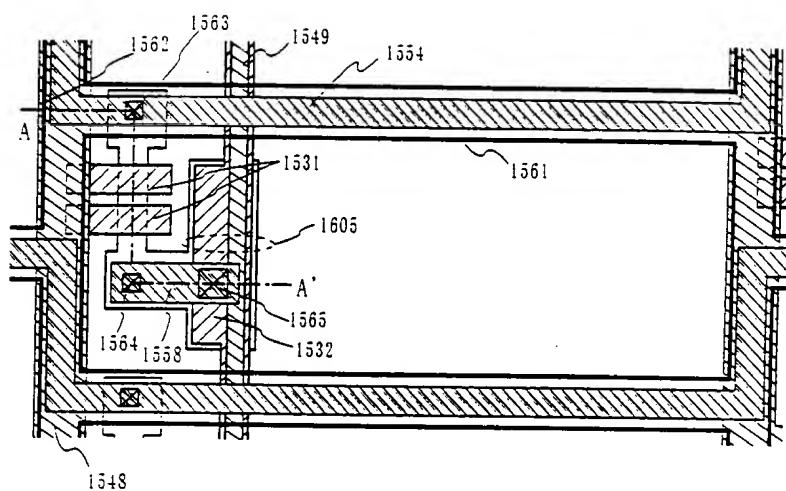
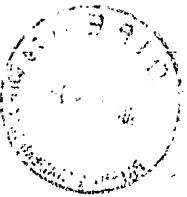
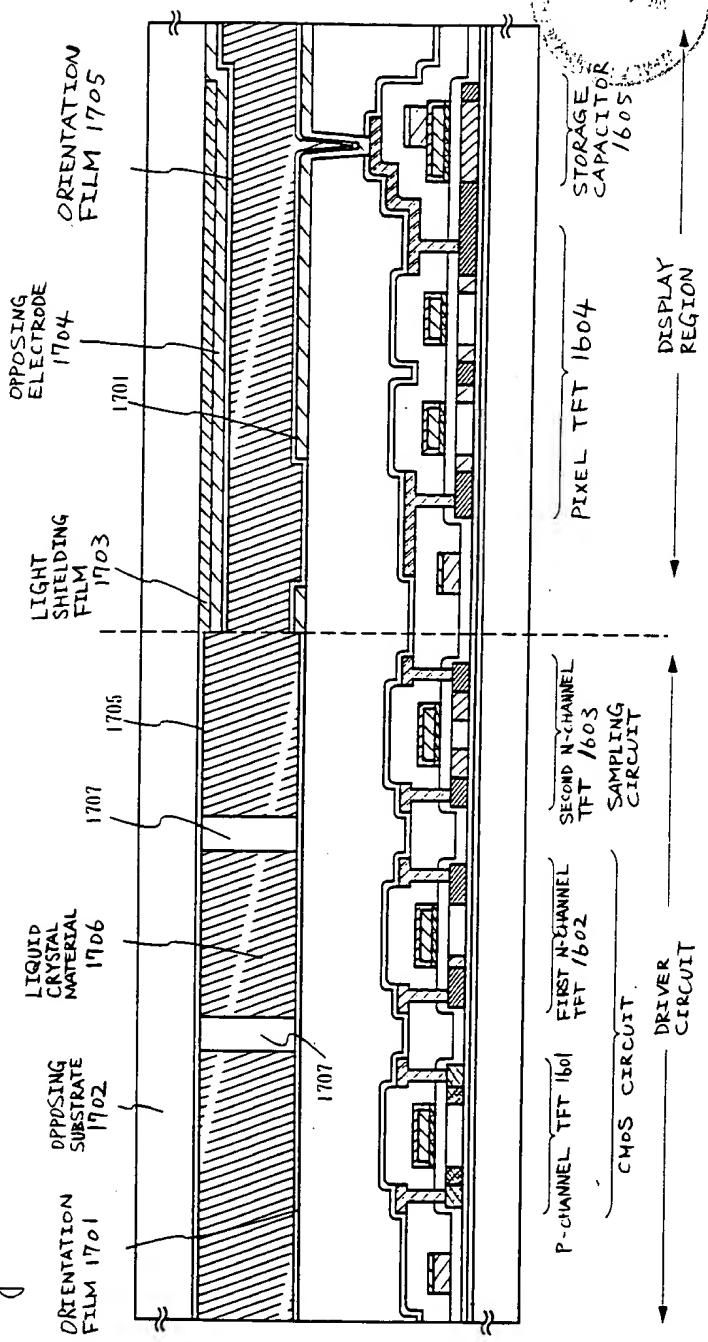


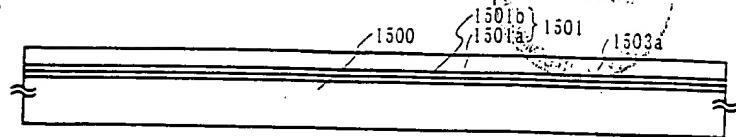
Fig. 19

Fig. 20



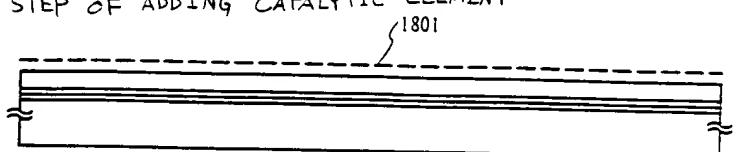
STEP OF FORMING AMORPHOUS SEMICONDUCTOR FILM

Fig. 21A



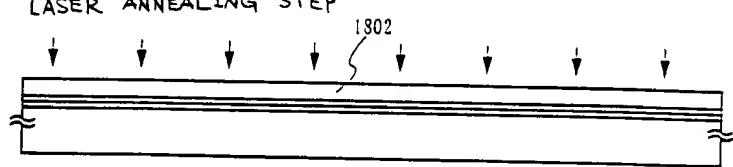
STEP OF ADDING CATALYTIC ELEMENT

Fig. 21B



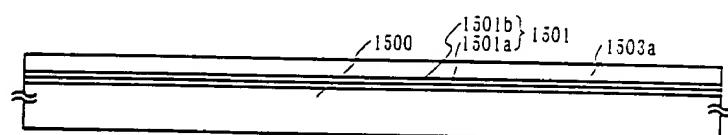
LASER ANNEALING STEP

Fig. 21C



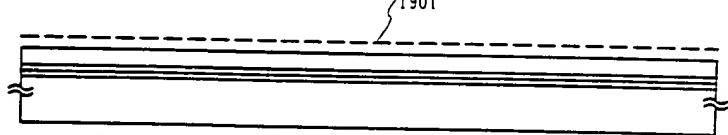
STEP OF FORMING AMORPHOUS SEMICONDUCTOR FILM

Fig. 22A



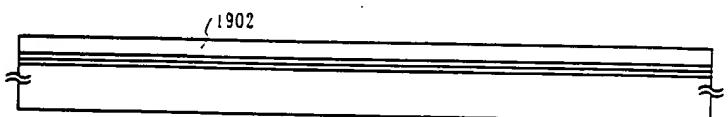
STEP OF ADDING CATALYTIC ELEMENT

Fig. 22B



CRYSTALLIZATION STEP (HEAT CRYSTALLIZATION)

Fig. 22C



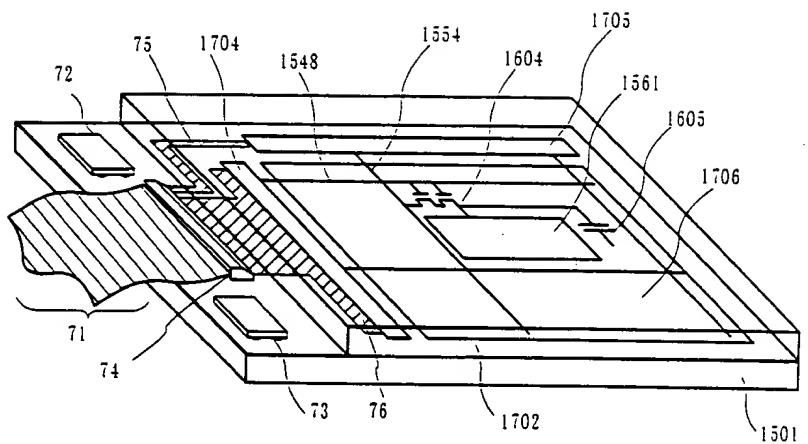
LASER ANNEALING STEP

Fig. 22D





Fig. 23



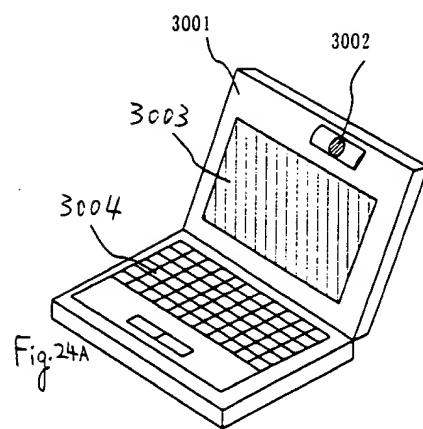


Fig. 24A

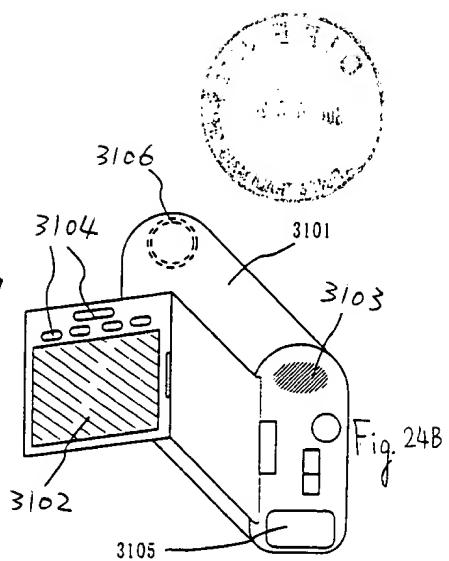


Fig. 24B

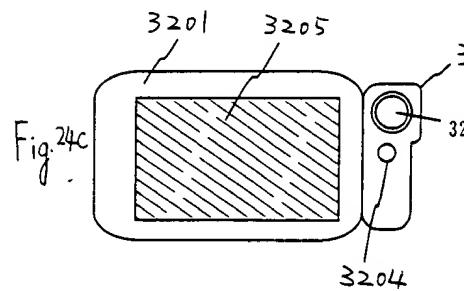


Fig. 24C

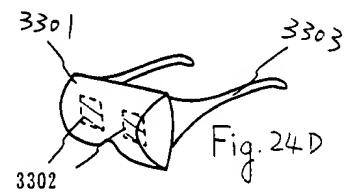


Fig. 24D

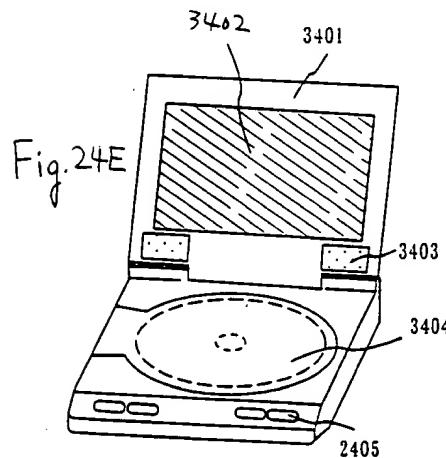


Fig. 24E

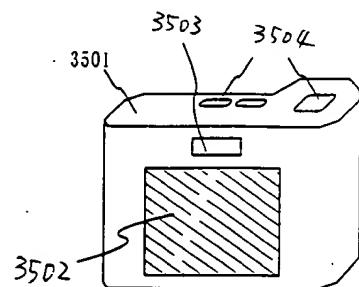


Fig. 24F

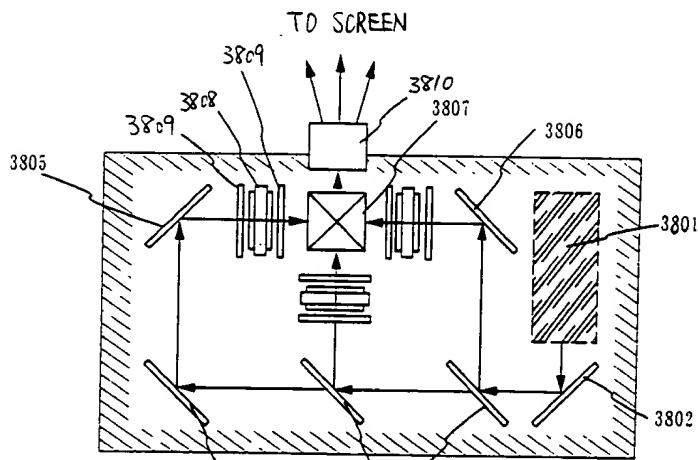
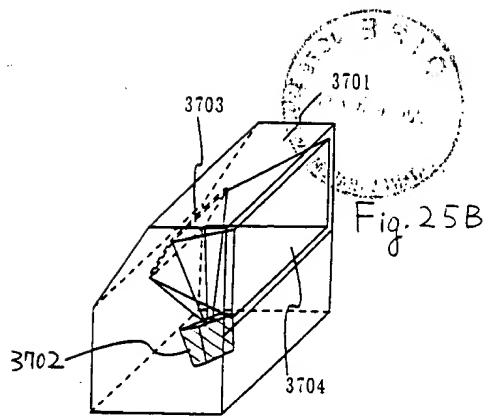
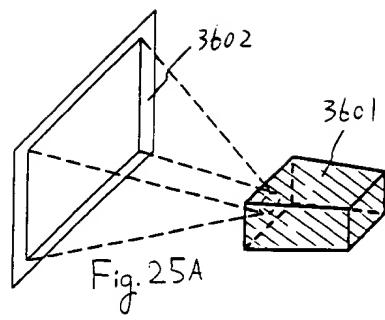


Fig. 25C PROJECTING APPARATUS (THREE-PLATE TYPE)

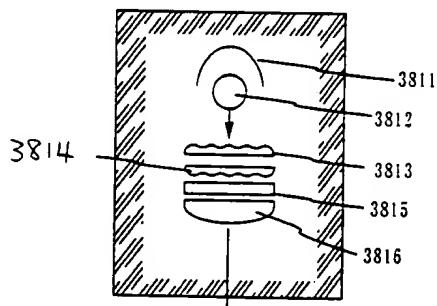


Fig. 25D LIGHT SOURCE OPTICAL SYSTEM

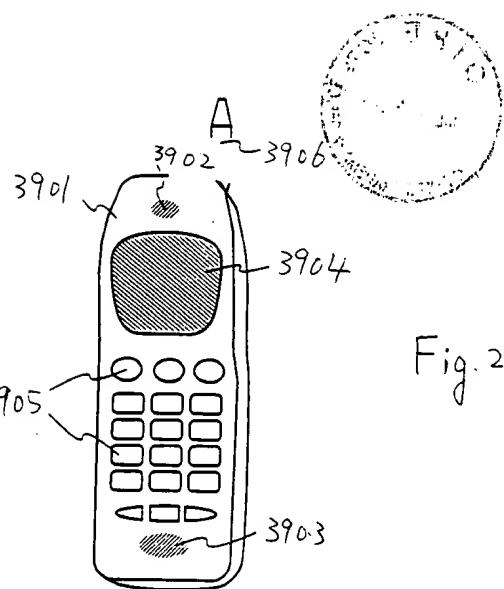


Fig. 26A

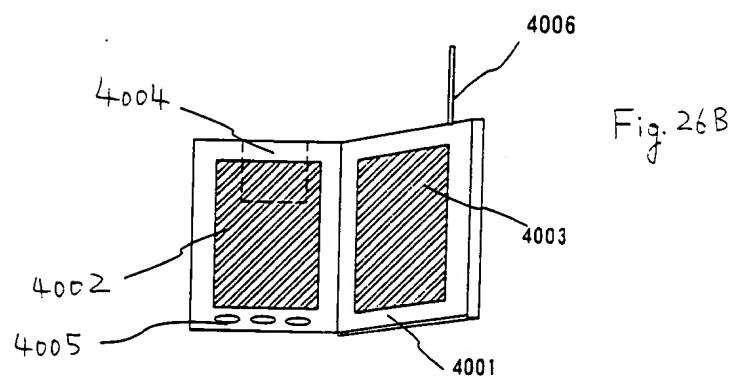


Fig. 26B

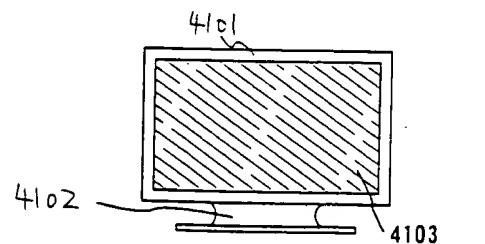


Fig. 26C